

# 2SB1132

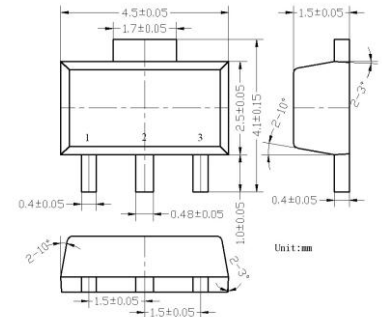
## 2SB1132 TRANSISTOR (PNP)

### Features:

Compliments 2SD1664

### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-32	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-1	A
$I_{CP}$	Collector Current -Pulsed	-2	A
$P_C$	Collector Power Dissipation	500	mW
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



1. BASE
2. COLLECTOR
3. EMITTER

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

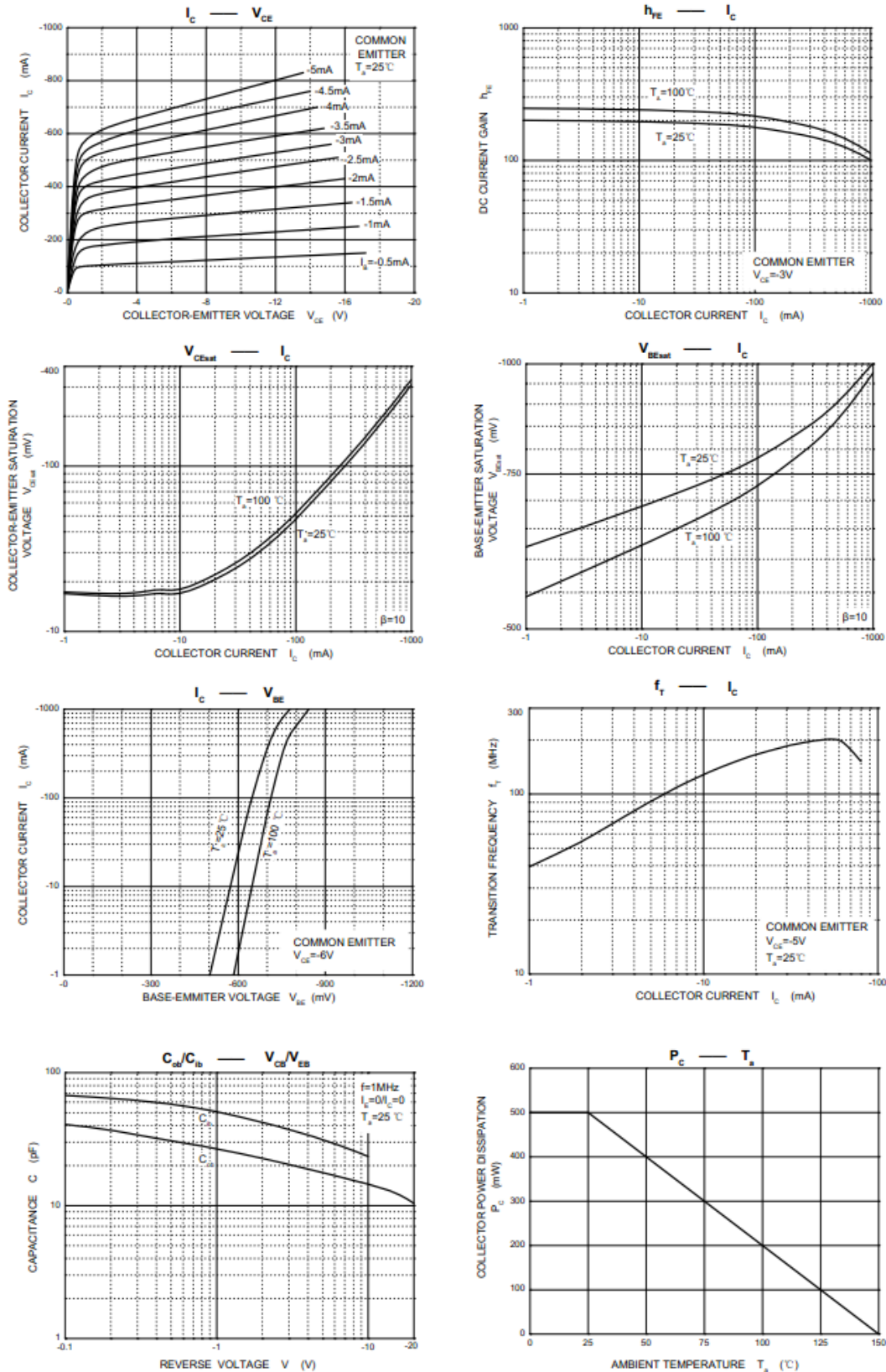
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20\text{V}, I_E = 0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -3\text{V}, I_C = -100\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.2	-0.5	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -50\text{mA}, f = 30\text{MHZ}$		150		MHZ
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHZ}$		20	30	PF

### CLASSIFICATION OF $h_{FE}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR

# Typical Characteristics

# 2SB1132



单击下面可查看定价，库存，交付和生命周期等信息

[>>YONGYUTAI\(永裕泰\)](#)